

General Description

The ZM042N04M combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

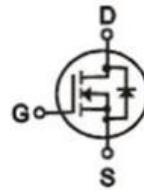
Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

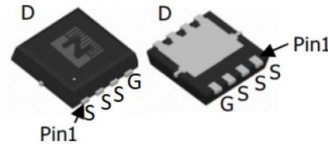
Product Summary



$$V_{DS} = 40V$$

$$R_{DS(ON)} = 5.5m\Omega$$

$$I_D = 45A$$



DFN3 x 3

Ordering Information:

Part NO.	ZM042N04M
Marking	042N04
Packing Information	REEL TAPE
Basic ordering unit (pcs)	5000

Absolute Maximum Ratings ($T_C = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_{D@TC=25^\circ C}$	45	A
	$I_{D@TC=75^\circ C}$	34	A
	$I_{D@TC=100^\circ C}$	28	A
Pulsed Drain Current ^①	I_{DM}	135	A
Total Power Dissipation	$P_{D@TC=25^\circ C}$	40	W
Total Power Dissipation	$P_{D@TA=25^\circ C}$	1.5	W
Operating Junction Temperature	T_J	-55 to 150	$^\circ C$
Storage Temperature	T_{STG}	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	E_{AS}	280	mJ

●Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}	-	-	3.1	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	83.3	°C/W
Soldering temperature, wave soldering for 10s	T_{sold}	-	-	265	°C

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=24A$		5.5	7	m Ω
		$V_{GS}=4.5V, I_D=12A$		7	9	m Ω
Forward Trans conductance	g_{FS}	$V_{DS}=25V, I_D=10A$		12		S
Source-drain voltage	V_{SD}	$I_S=24A$			1.28	V

●Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C_{iss}	f = 1MHz V _{DS} =25V	-	2450	-	pF
Output capacitance	C_{oss}		-	410	-	
Reverse transfer capacitance	C_{rss}		-	270	-	

●Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q_g	V _{DD} =25V	-	26	-	nC
Gate - Source charge	Q_{gs}	I _D = 8A	-	8	-	
Gate - Drain charge	Q_{gd}	V _{GS} = 10V	-	13	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

Fig.1 Power Dissipation

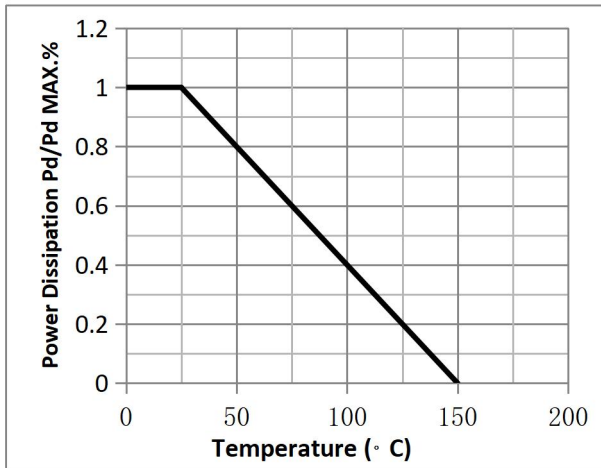


Fig.2 Typical output Characteristics

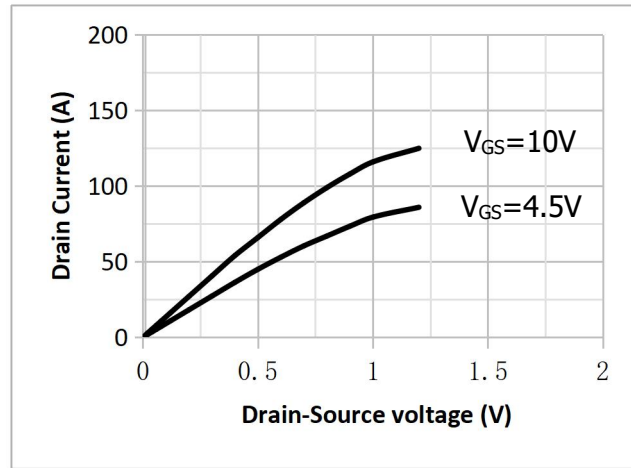


Fig.3 Threshold Voltage V.S Junction Temperature

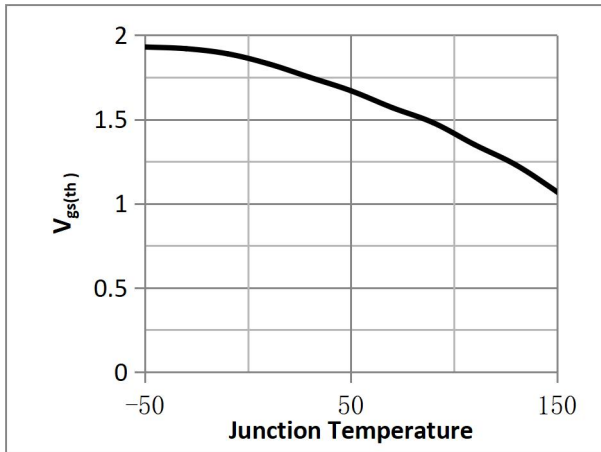


Fig.4 Resistance V.S Drain Current

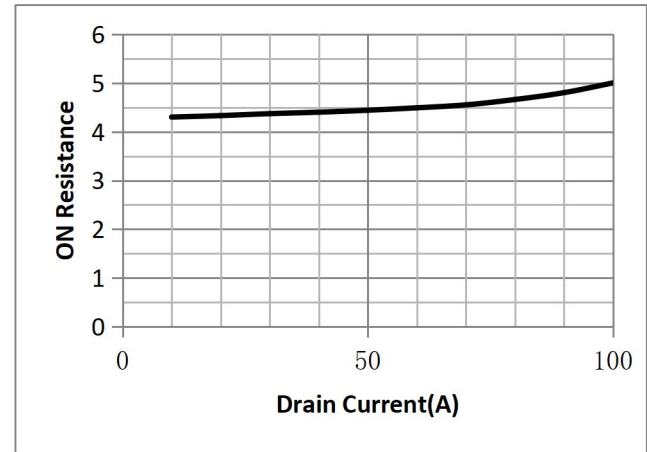


Fig.5 On-Resistance VS Gate Source Voltage

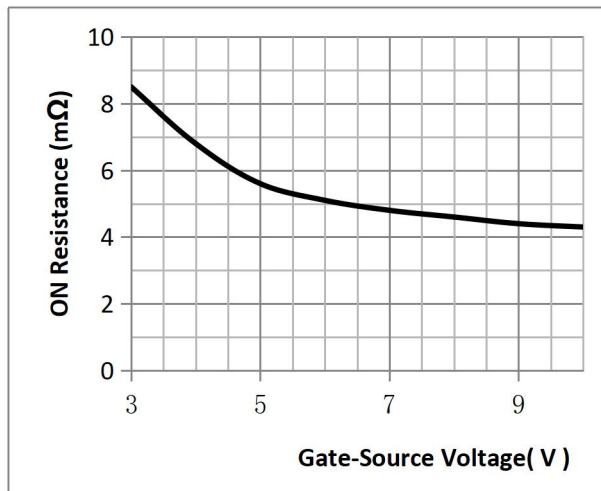


Fig.6 On-Resistance V.S Junction Temperature

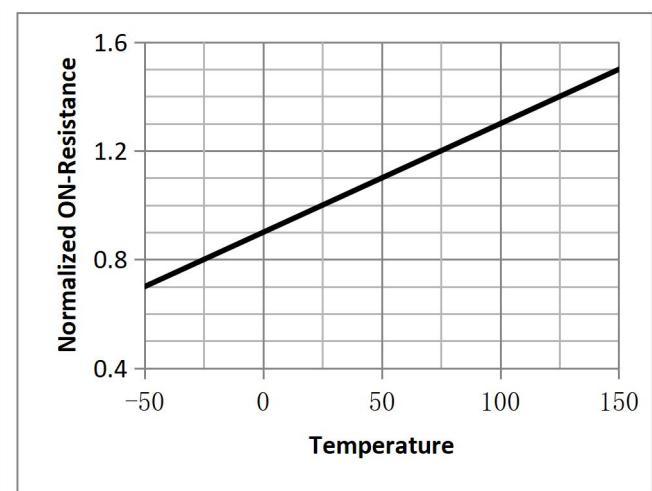


Fig.7 Switching Time Measurement Circuit

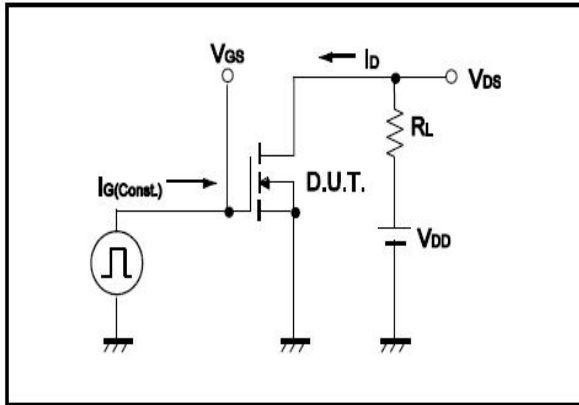


Fig.8 Gate Charge Waveform

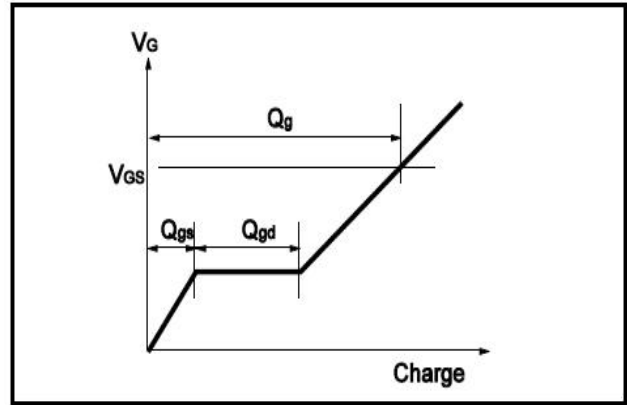


Fig.9 Switching Time Measurement Circuit

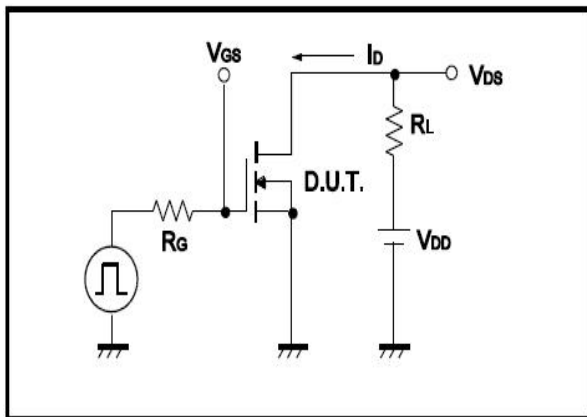


Fig.10 Gate Charge Waveform

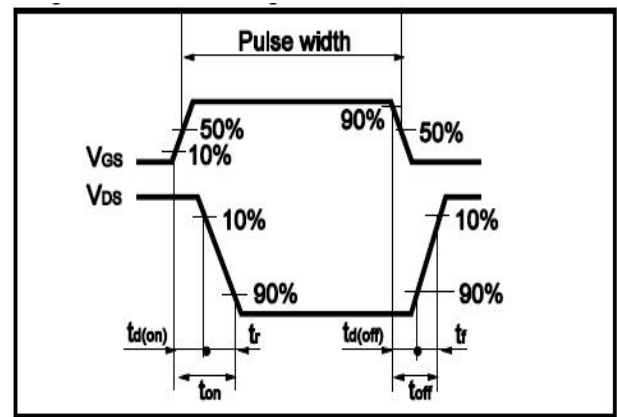


Fig.11 Avalanche Measurement Circuit

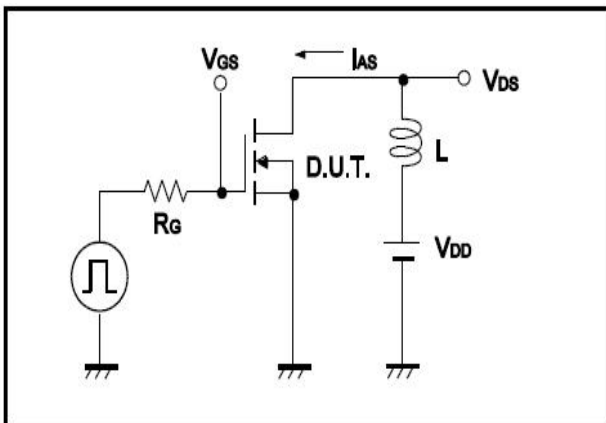
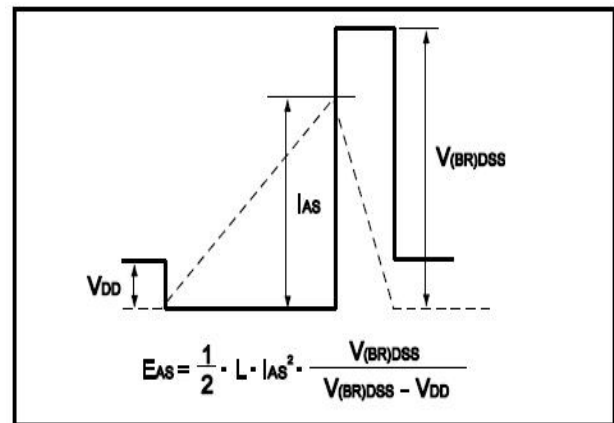


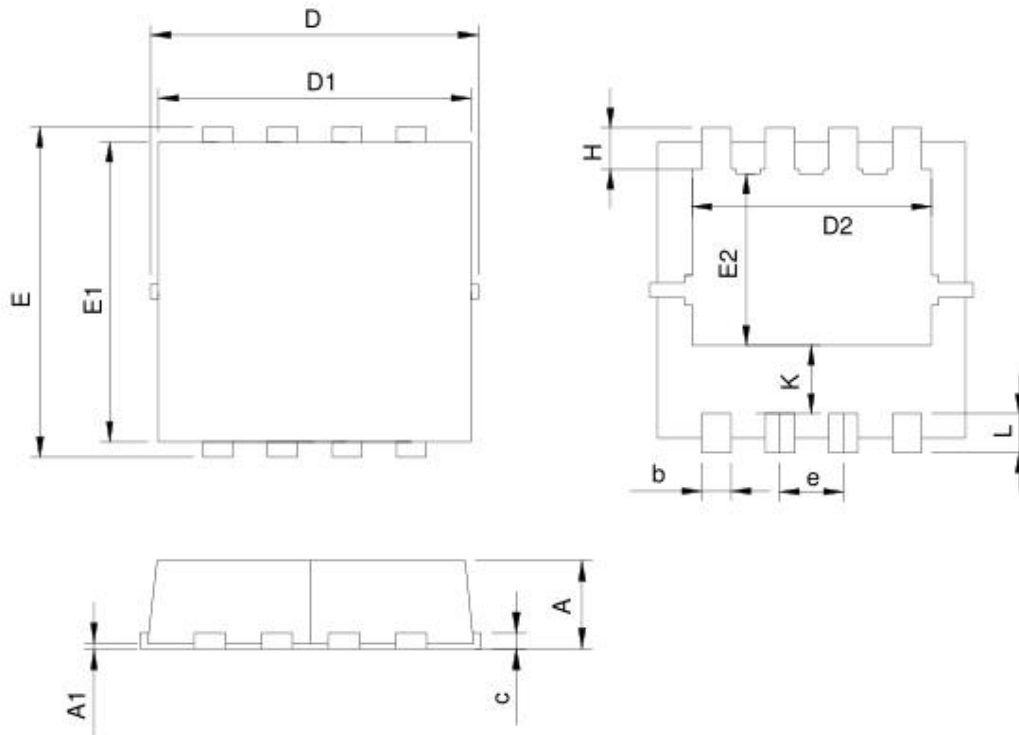
Fig.12 Avalanche Waveform





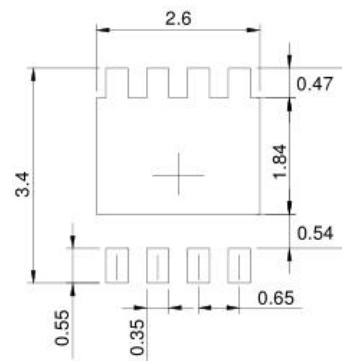
●Dimensions (DFN3×3)

Unit: mm



SYMBOL	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm